

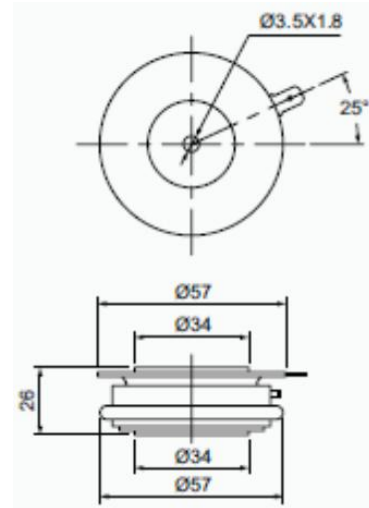
Fast Recovery Diode

FEATURES

- Full diffusion process, flat type ceramic tube package
- Double sides cooling, High current
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- High power converters
- AC/DC switching
- Phase controlled rectifying



ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_R	Repetitive Peak Reverse Voltage		4500	V
$I_{F(AV)}$	Average Forward Current	$T_C=85^\circ\text{C}$; $f=50\text{Hz}$	330	A
I_{FSM}	Surge Forward Current	$t_p=10\text{ms}$	6000	A
T_J	Junction Temperature		-40~150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range		-40~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.4	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Forward Voltage drop	$I_F= 1200A, T_J= 25^{\circ}C$	3.9	V
I_{RRM}	Instantaneous Reverse Current	$V_{RM}=V_{RRM}$	100	mA
t_{rr}	Reverse Recovery Time	$I_{FM}= 1000A, -di/dt=250A/\mu s;$ $V_R=1000V$	4	μs